Power Transistors

Panasonic

2SB0942 (2SB942), 2SB0942A (2SB942A)

Silicon PNP epitaxial planar type

For low-frequency power amplification

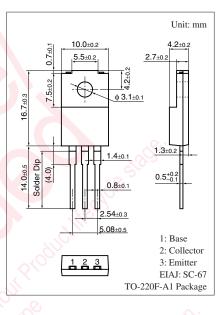
Complementary to 2SD1267, 2SD1267A

Features

- \bullet High forward current transfer ratio $h_{F\!E}$ which has satisfactory linearity
- \bullet Large collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- Full-pack package which can be installed to the heat sink with one screw

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0942	V _{CBO}	-60	v
(Emitter open)	2SB0942A		-80	
Collector-emitter voltage	2SB0942	V _{CEO}	-60	V
(Base open)	2SB0942A		-80	
Emitter-base voltage (Col	V _{EBO}	-5	v	
Collector current		I _C	-4	А
Peak collector current	I _{CP}	-8	А	
Collector power		P _C	40	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	<u>∽°C</u>	
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Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

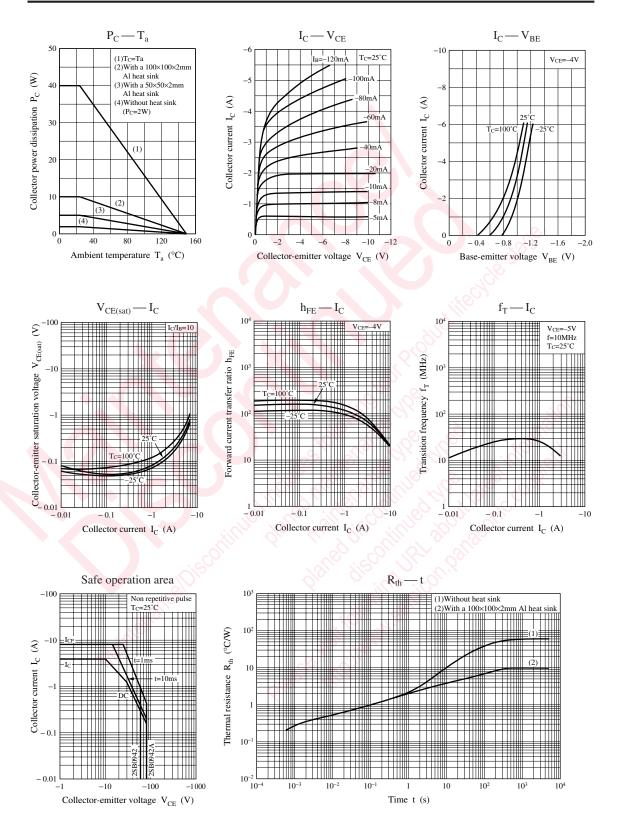
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0942	V _{CEO}	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = 0$	-60	- Clip		V
(Base open)	2SB0942A		Stor Ro Sto Siller	-80	S		
Base-emitter voltage		V _{BE}	$V_{CE} = -4 V, I_C = -3 A$	S		-2	V
Collector-emitter	2SB0942	I _{CES}	$V_{CE} = -60 \text{ V}, V_{BE} = 0$	O^{X}		-400	μΑ
cutoff current (E-B short)	2SB0942A		$V_{CE} = -80 \text{ V}, V_{BE} = 0$			-400	
Collector-emitter cutoff current	(Base open)	I _{CEO}	$V_{CE} = -30 \text{ V}, I_B = 0$			-700	μΑ
Emitter-base cutoff current (Collector open)		I _{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio		h _{FE1} *	$V_{CE} = -4 V, I_C = -1 A$	40		250	—
		h _{FE2}	$V_{CE} = -4 V, I_C = -3 A$	15			
Collector-emitter saturation	voltage	V _{CE(sat)}	$I_{\rm C} = -4$ A, $I_{\rm B} = -0.4$ A			-1.5	V
Transition frequency		f _T	$V_{CE} = -10 \text{ V}, I_C = -0.1 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time		t _{on}	$I_C = -4 A, I_{B1} = -0.4 A, I_{B2} = 0.4 A$		0.2		μs
Storage time		t _{stg}	$V_{\rm CC} = -50 \text{ V}$		0.5		μs
Fall time		t _f			0.2		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

Rank	R	Q	Р
h _{FE1}	40 to 90	70 to 150	120 to 250

Note) The part numbers in the parenthesis show conventional part number.

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